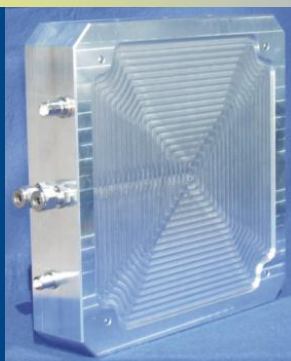


# **Diagnostics for Machine Protection at FERMI@Elettra**

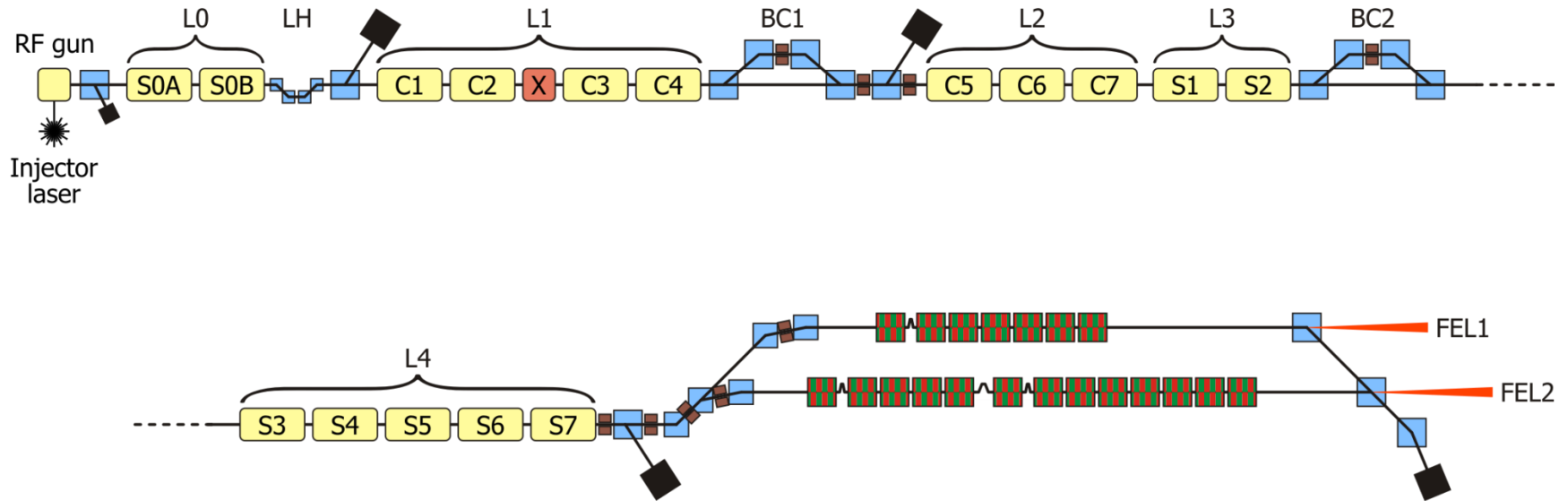


L. Fröhlich, A. I. Bogani, K. Casarin, G. Cautero, G. Gaio,  
 F. Giacuzzo, D. Giuressi, A. Gubertini, R. H. Menk, E. Quai,  
 G. Scalamera, A. Vascotto (Sincrotrone Trieste, Basovizza, Italy)  
 L. Catani (INFN, Rome, Italy), D. Di Giovenale

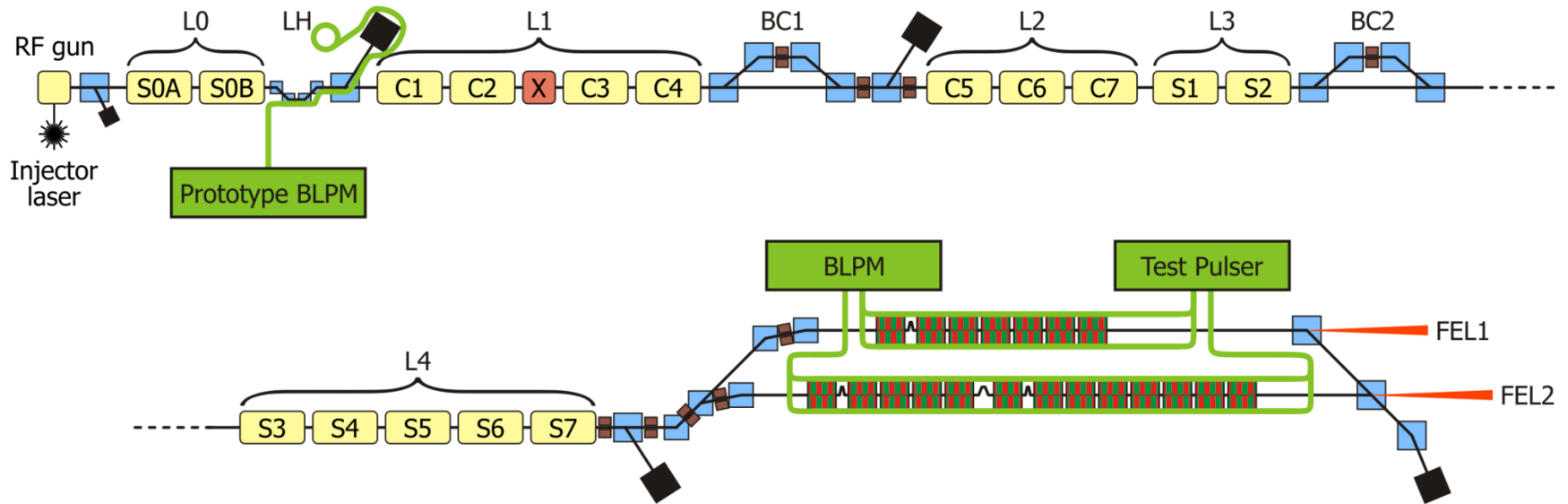
- FERMI@Elettra
- MPS architecture
- General features
  
- Subsystems:
  - Fiber beam loss position monitors
  - Ionization chambers
  - RADFET online dosimetry



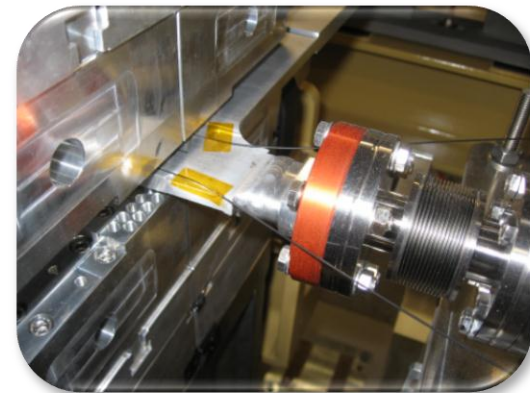


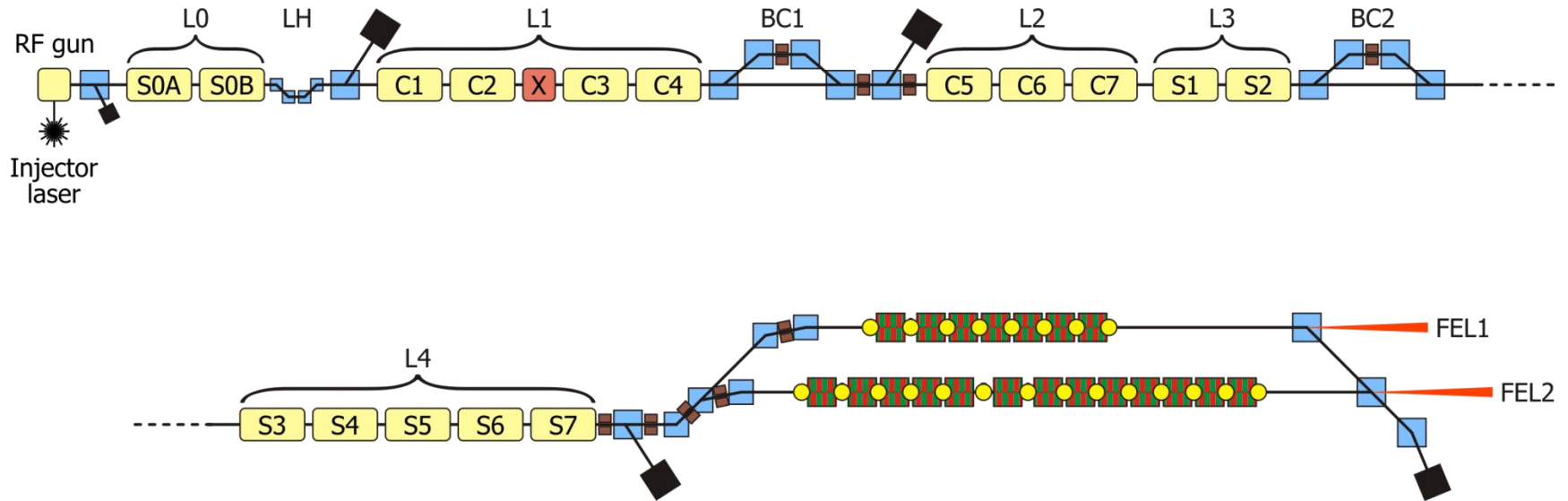


	<b>Energy</b>	<b>Bunch Charge</b>	<b>Repetition Rate</b>	<b>Beam Power</b>
Typical	1.2 GeV	350 pC	10 Hz	4.2 W
Design	1.5 GeV	1 nC	50 Hz	75 W

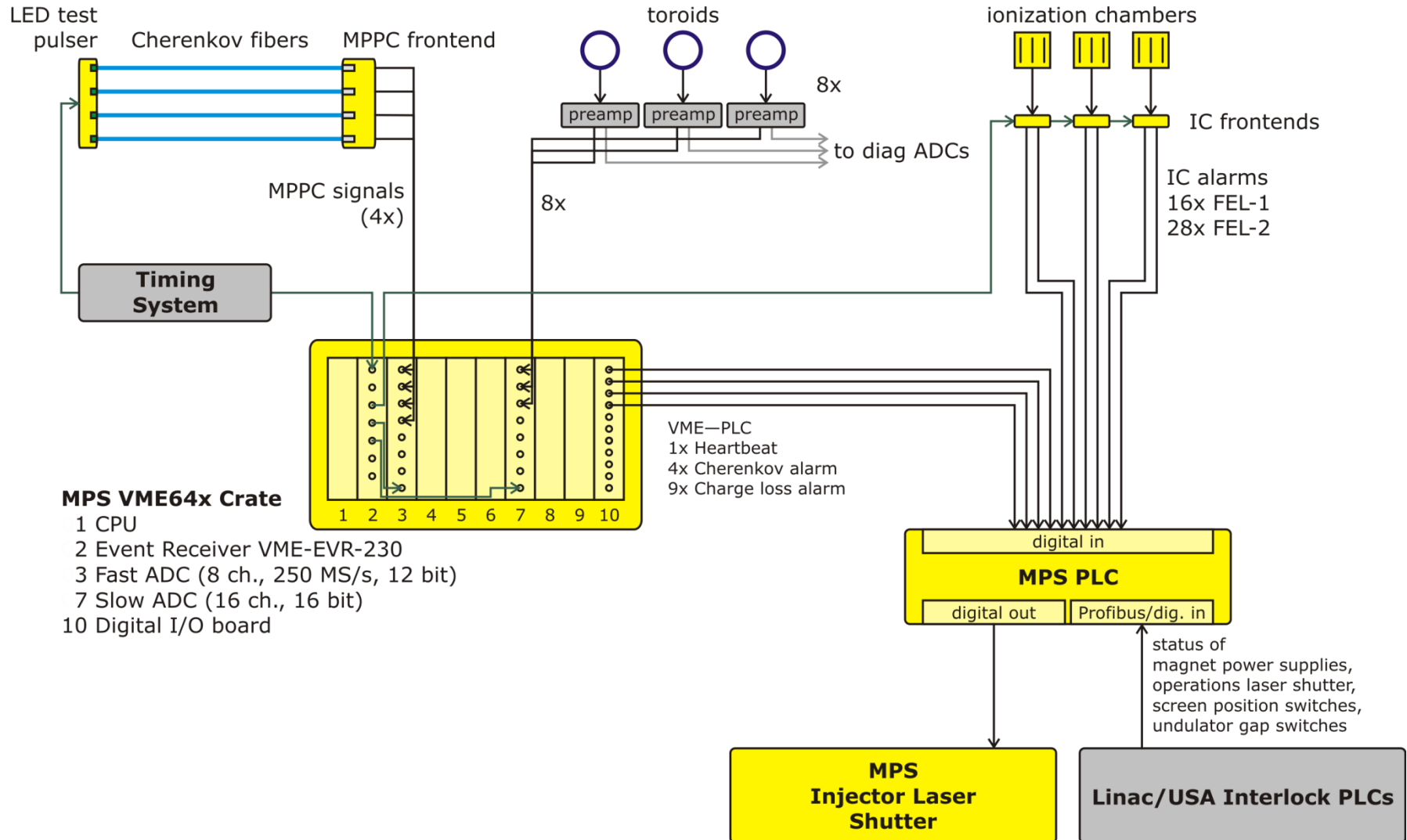


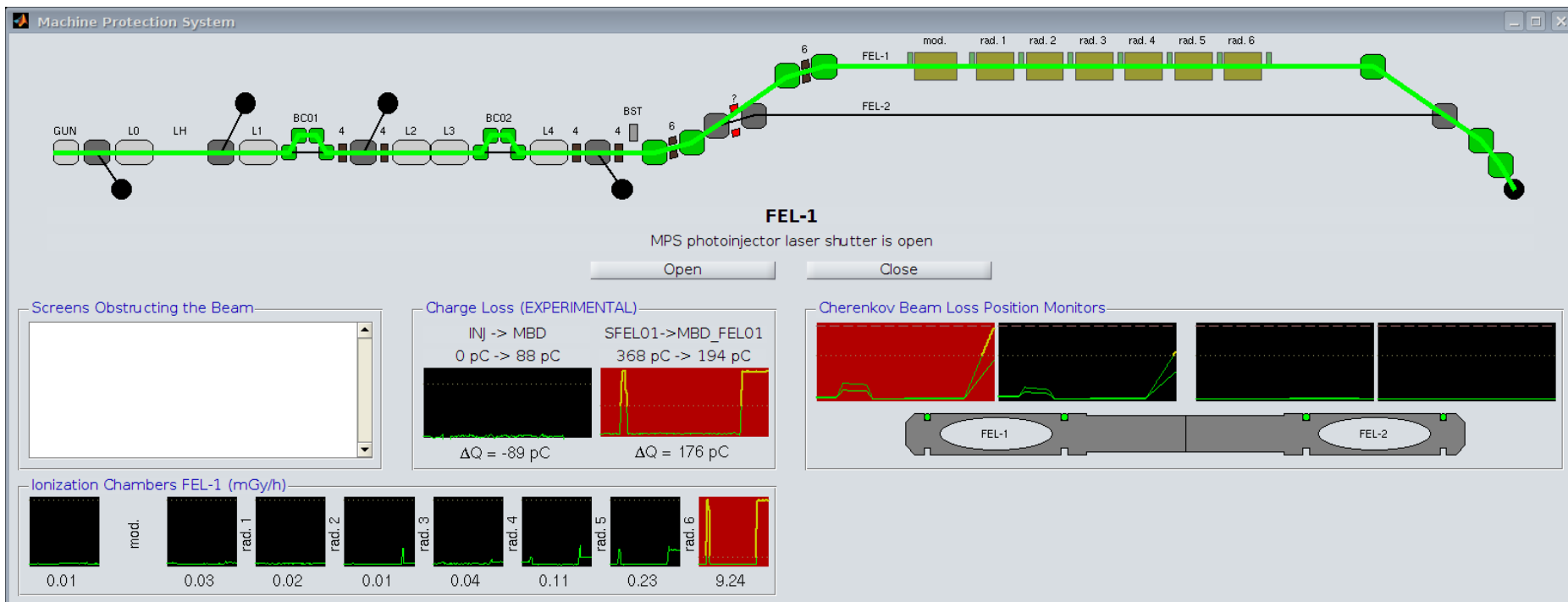
## Cherenkov Fiber Beam Loss Position Monitors (BLPMs)





## Ionization Chamber Beam Loss Monitors (BLMs)



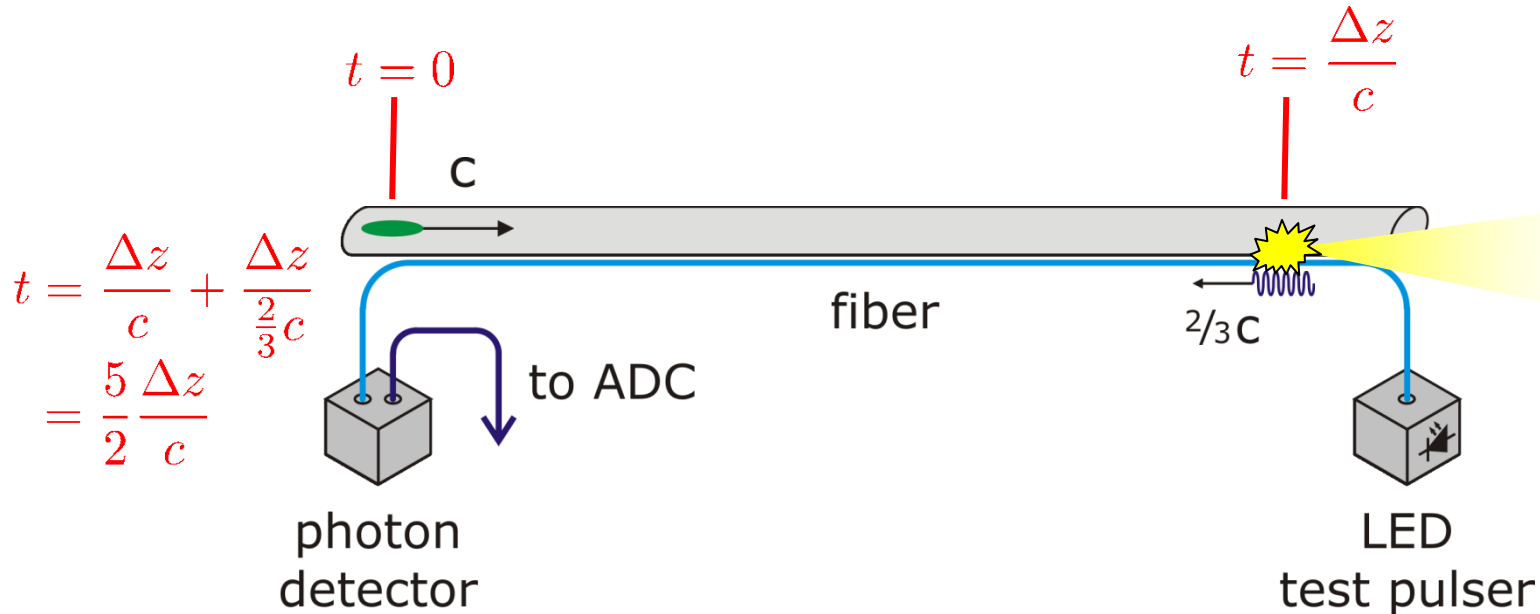




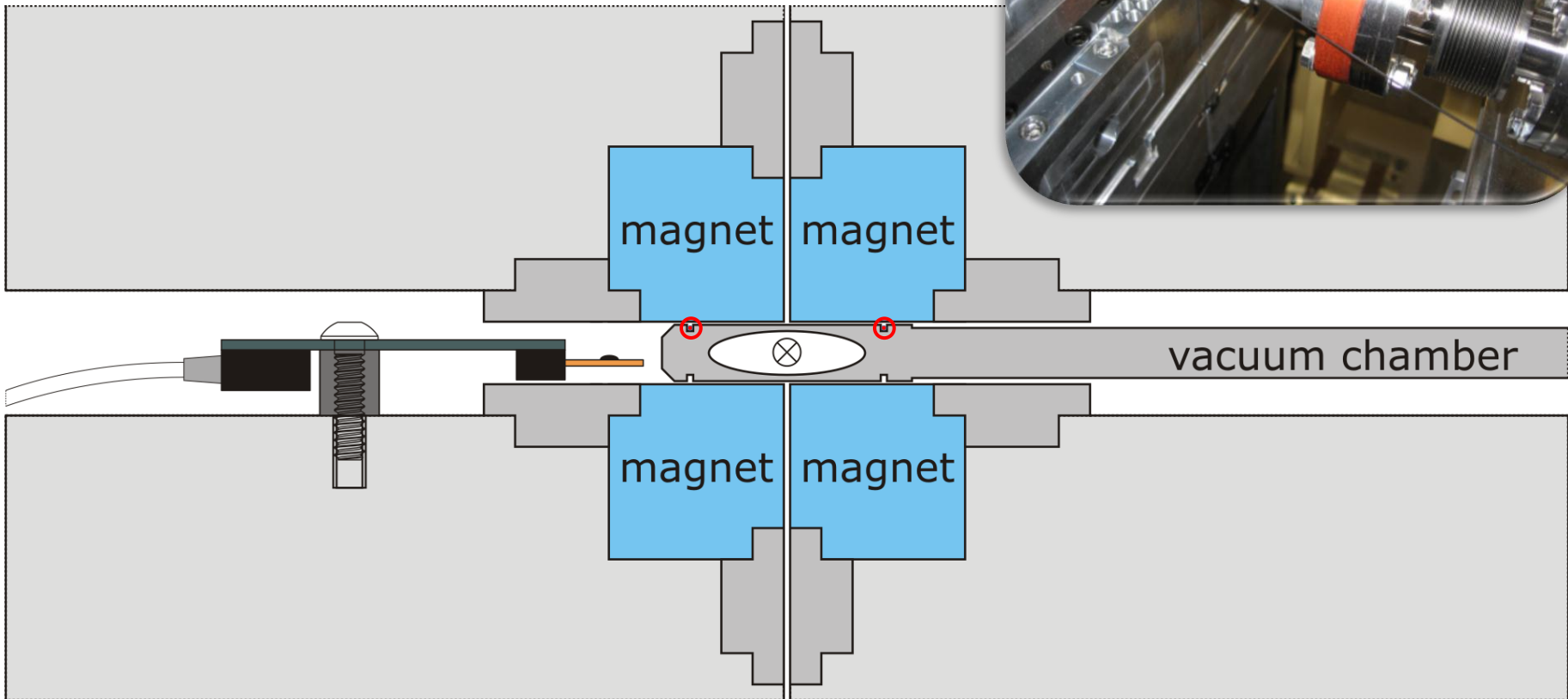
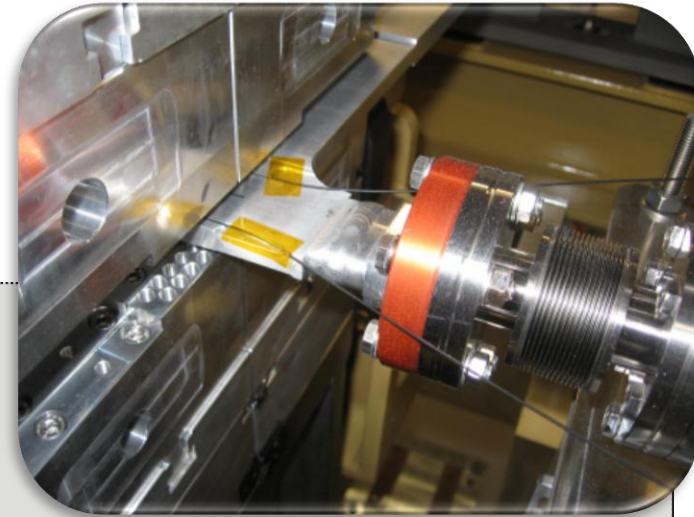
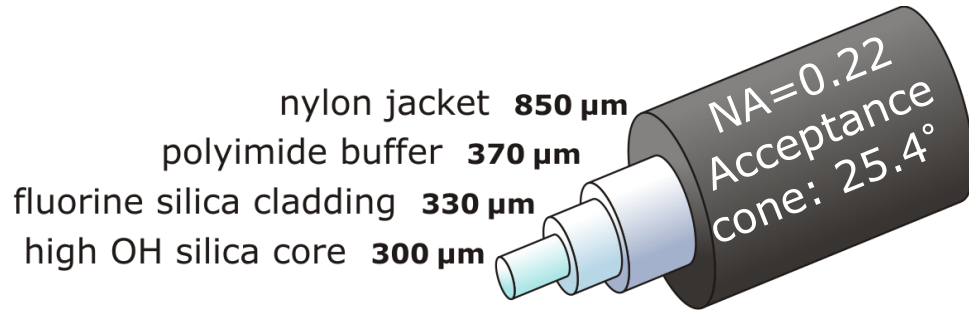
# Cherenkov Fiber Beam Loss Position Monitor

More information:

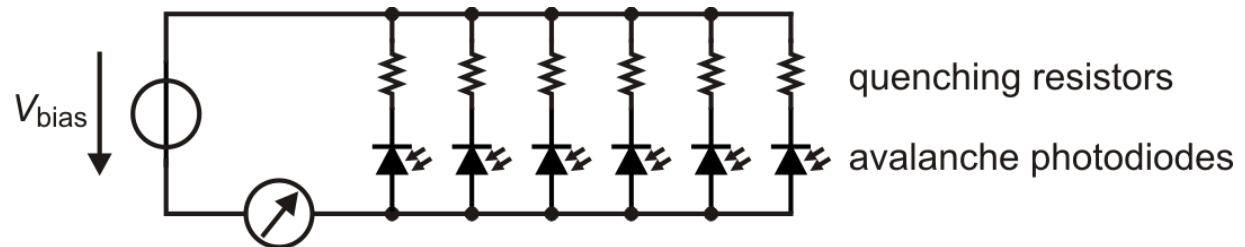
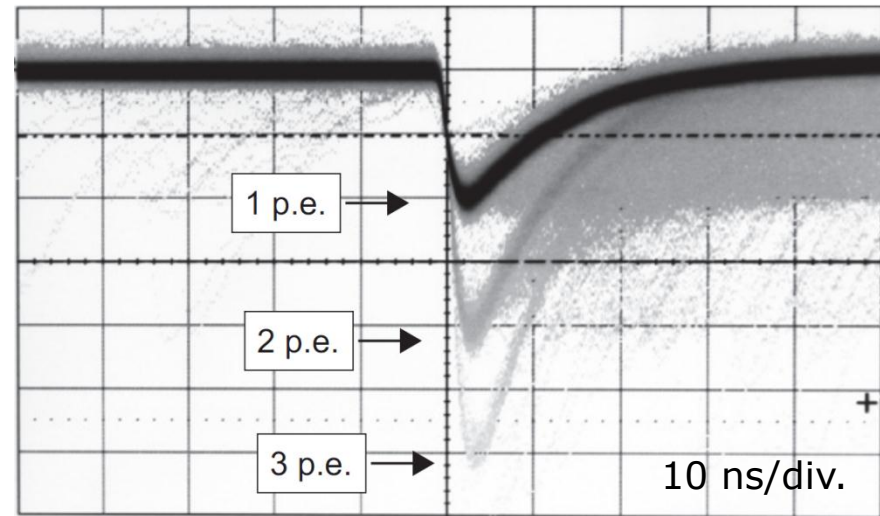
D. Di Giovenale, L. Catani, L. Fröhlich, "A read-out system for online monitoring of intensity and position of beam losses in electron linacs", Nucl. Instr. & Meth. A 665, pp. 33-39, 2011.

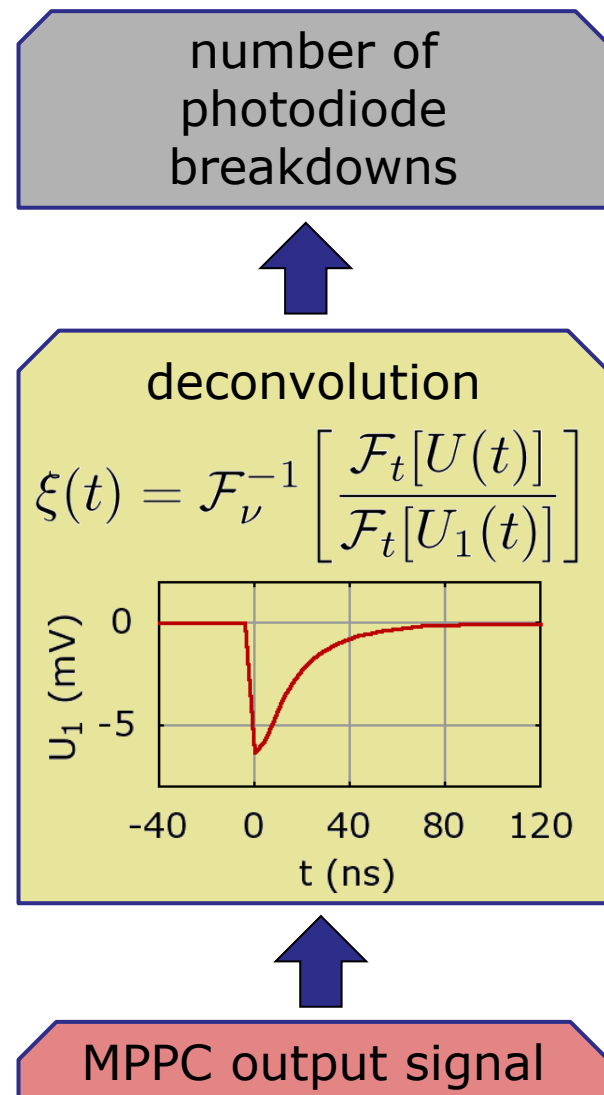
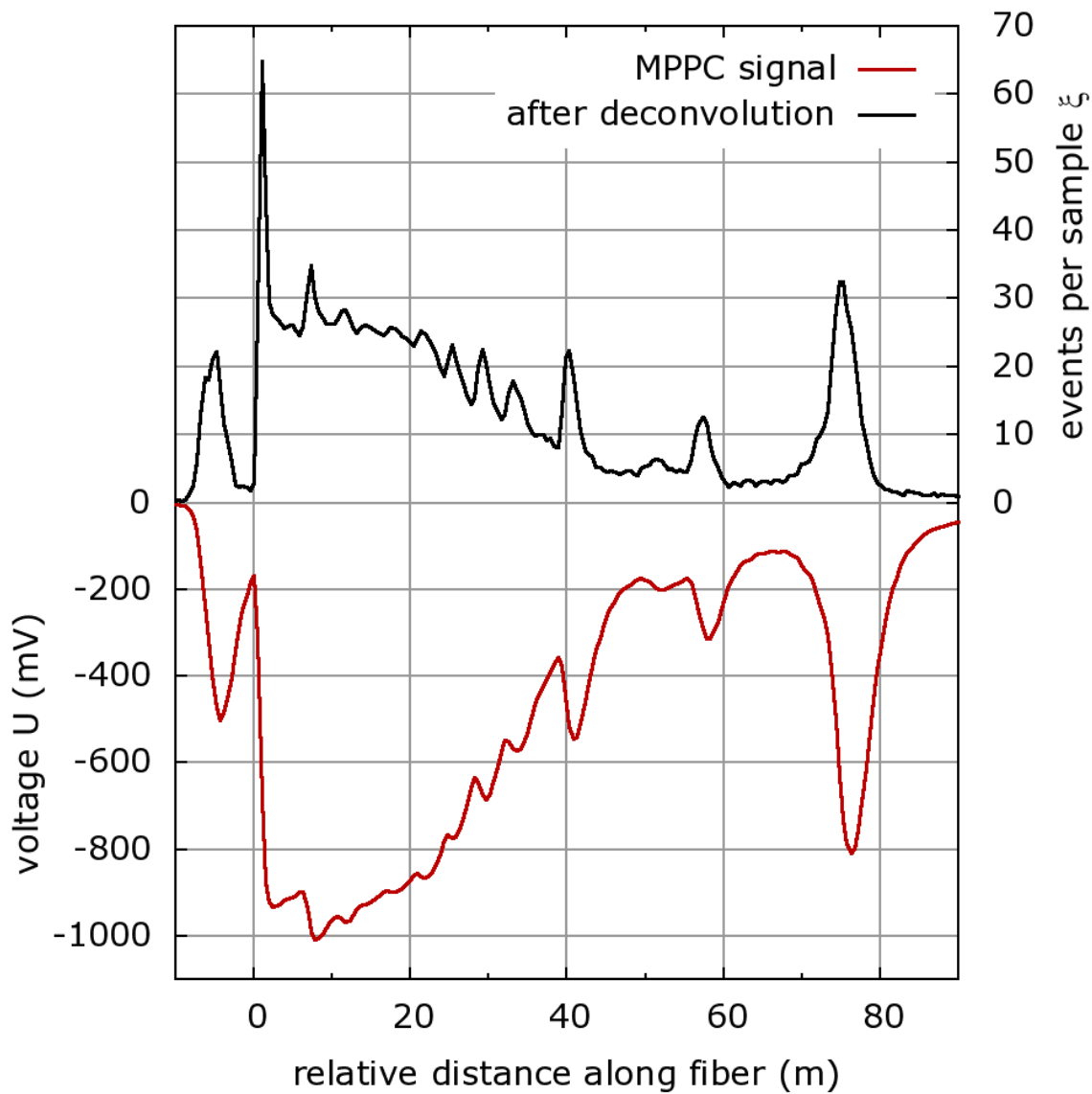


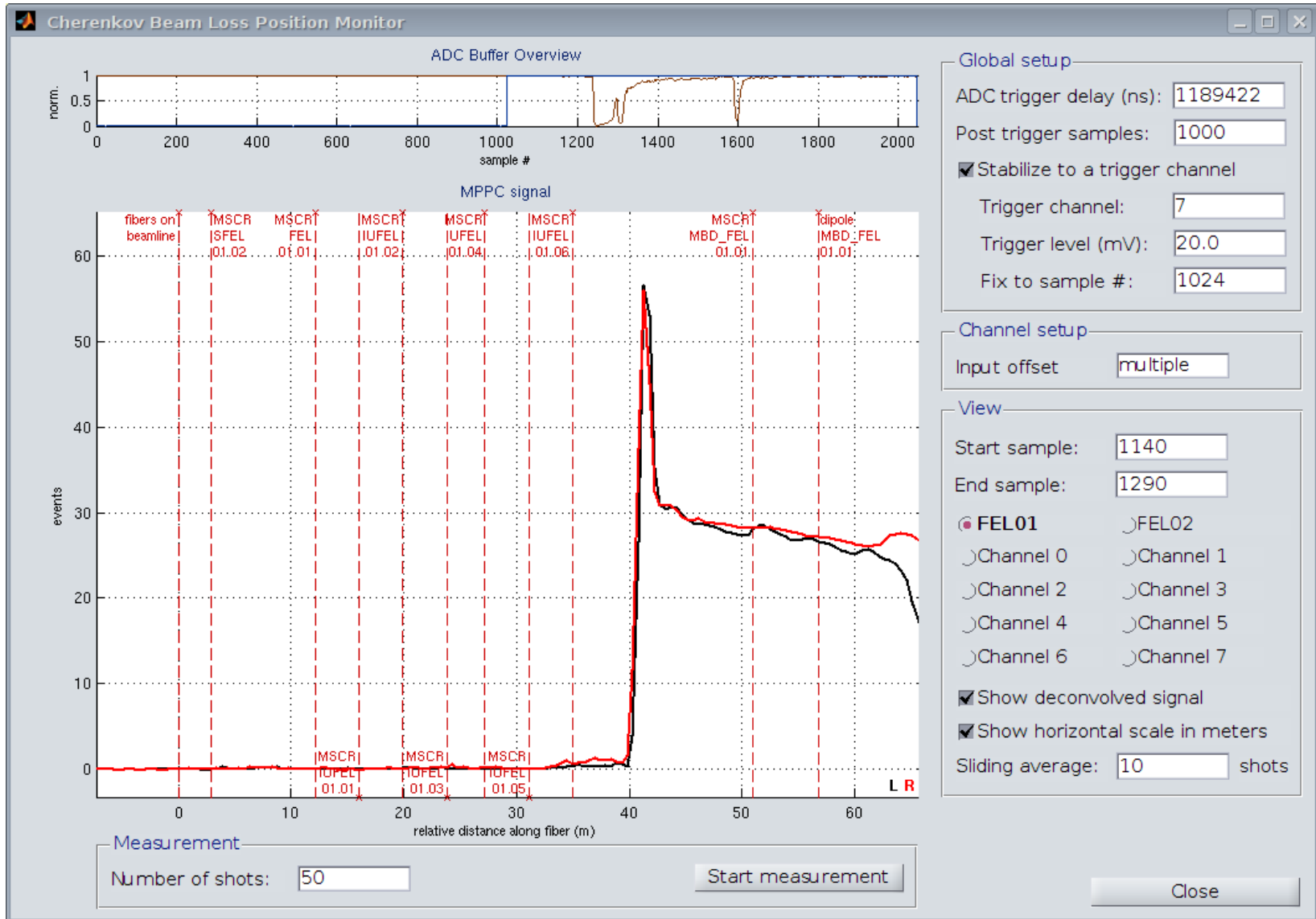
250 MS/s ADC → longitudinal resolution ~50 cm



- Array of avalanche photodiodes (APDs) connected in parallel
- Reverse bias  $\rightarrow$  photon causes APD breakdown
- Photomultiplier-like gain
- Dynamic range limited by number of APDs
- Rise time: some 100 ps
- Hamamatsu S10362-11-050U:  
400 APDs at  $\sim 70$  V reverse bias



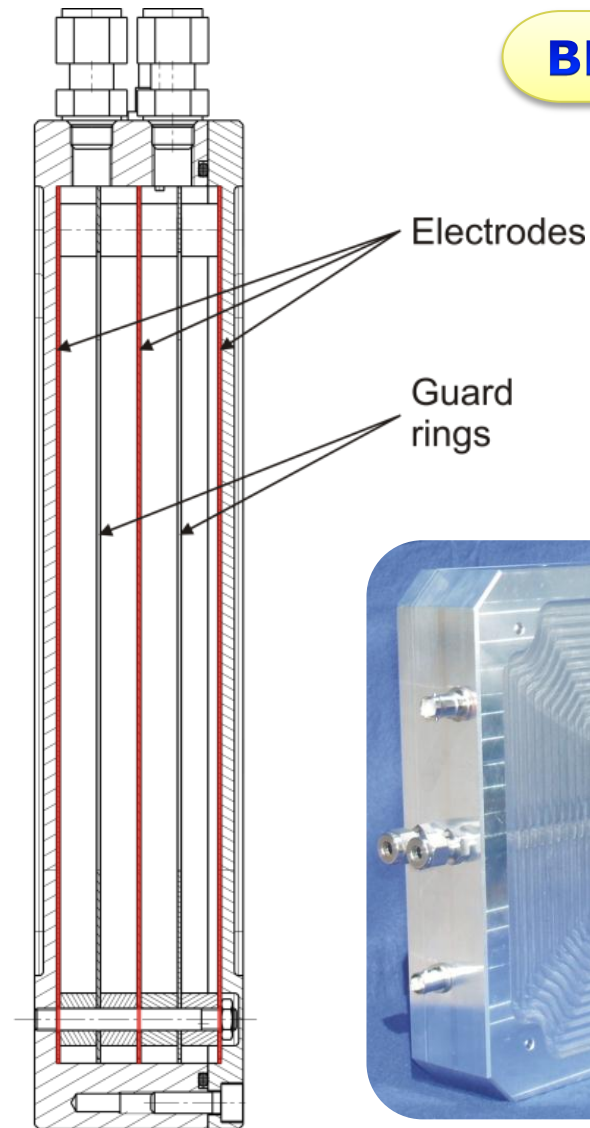




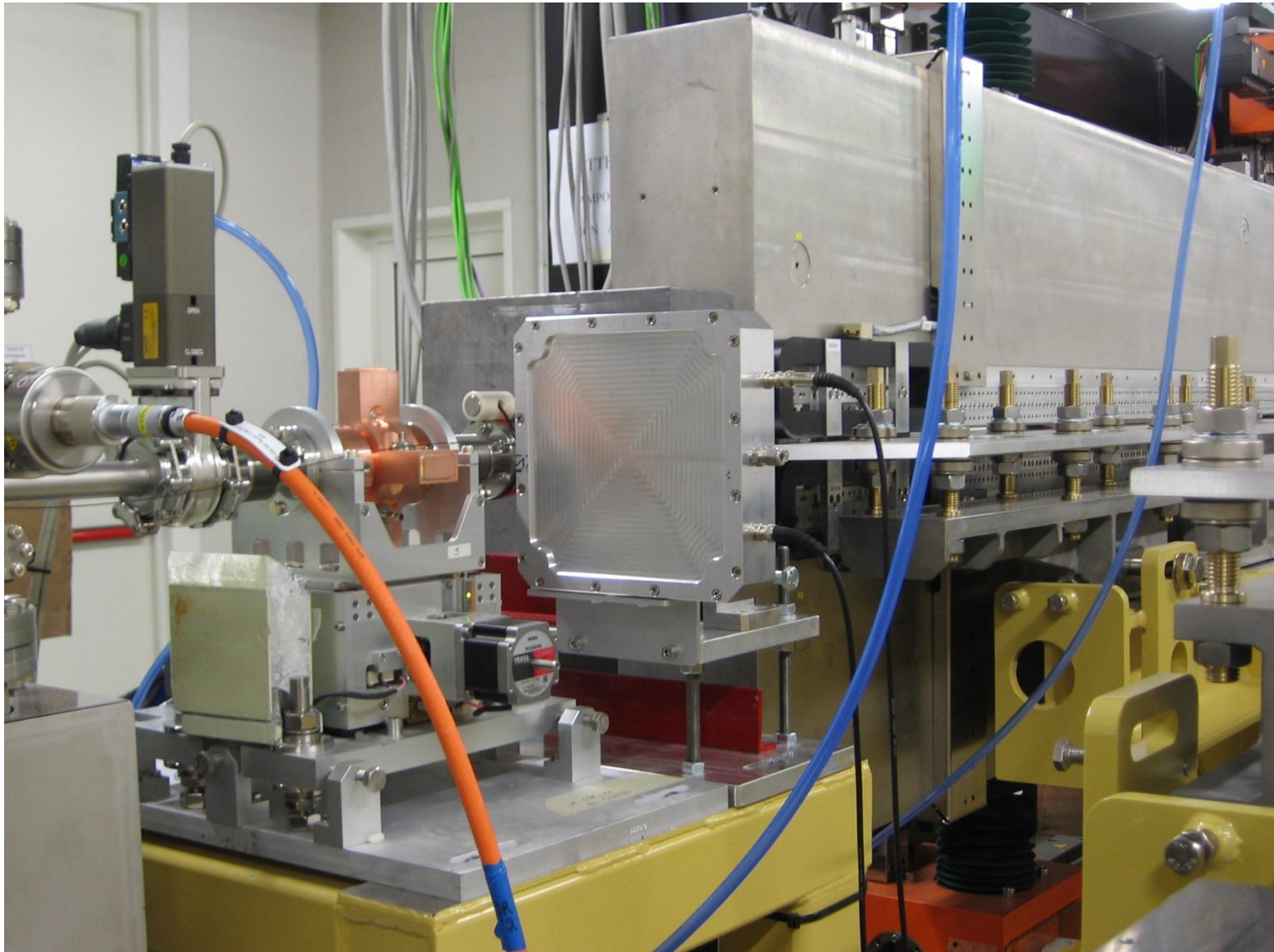
# Ionization Chambers

- Milled aluminum enclosure
- Electrodes: printed circuit boards
- Use in air or with gas flux
- Volume:  
1.3 l
- Voltage:  
up to 1000 V
- Sensitivity (air):  
 $\sim 46 \mu\text{C}/\text{Gy}$
- Leakage current:  
 $\ll 200 \text{ fA}$  (at 1000 V)
- Fermi:  
1 ionization chamber in air  
per undulator segment (19 total)

**BLM-IC02**





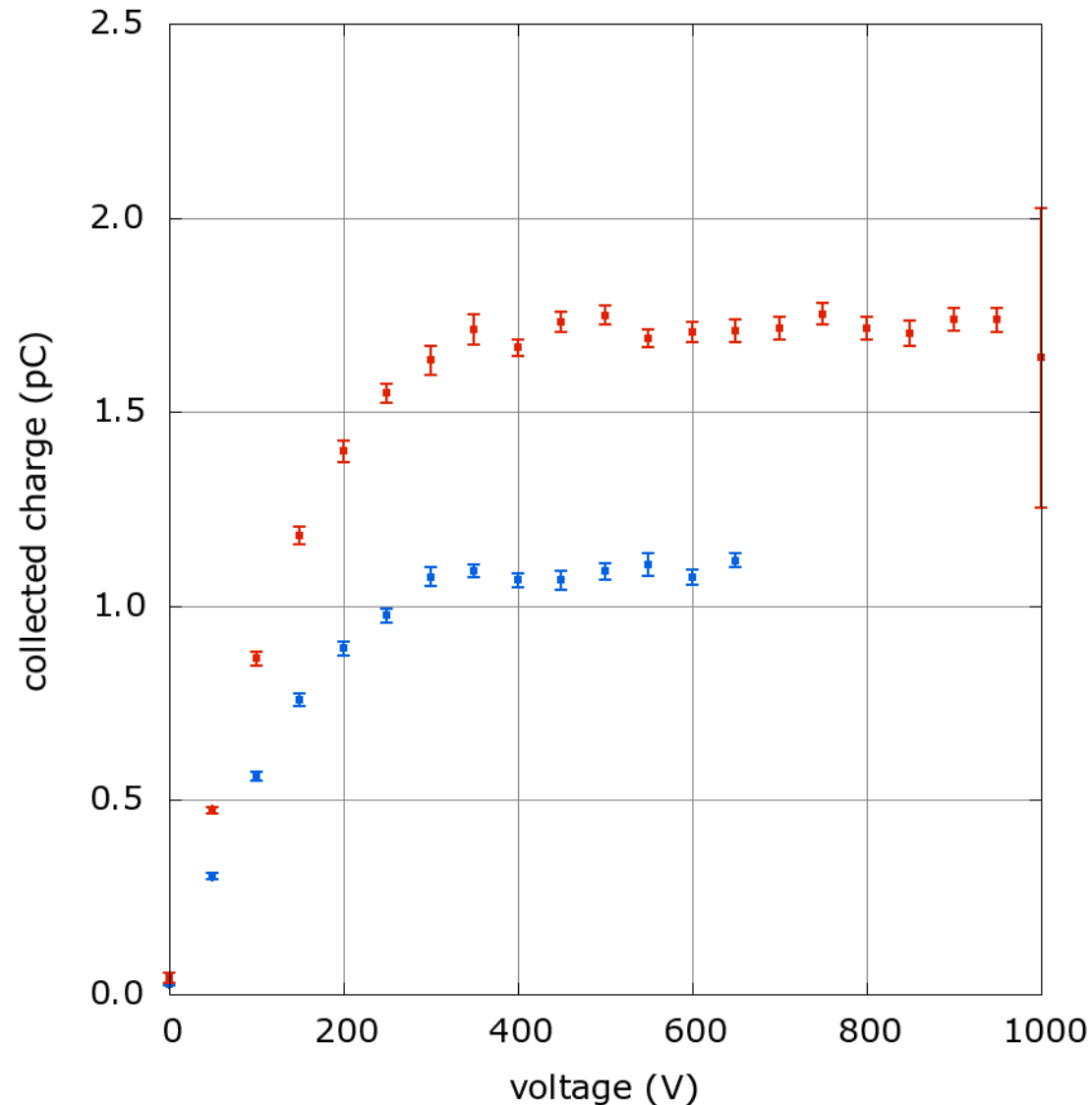


**XPi DAS**

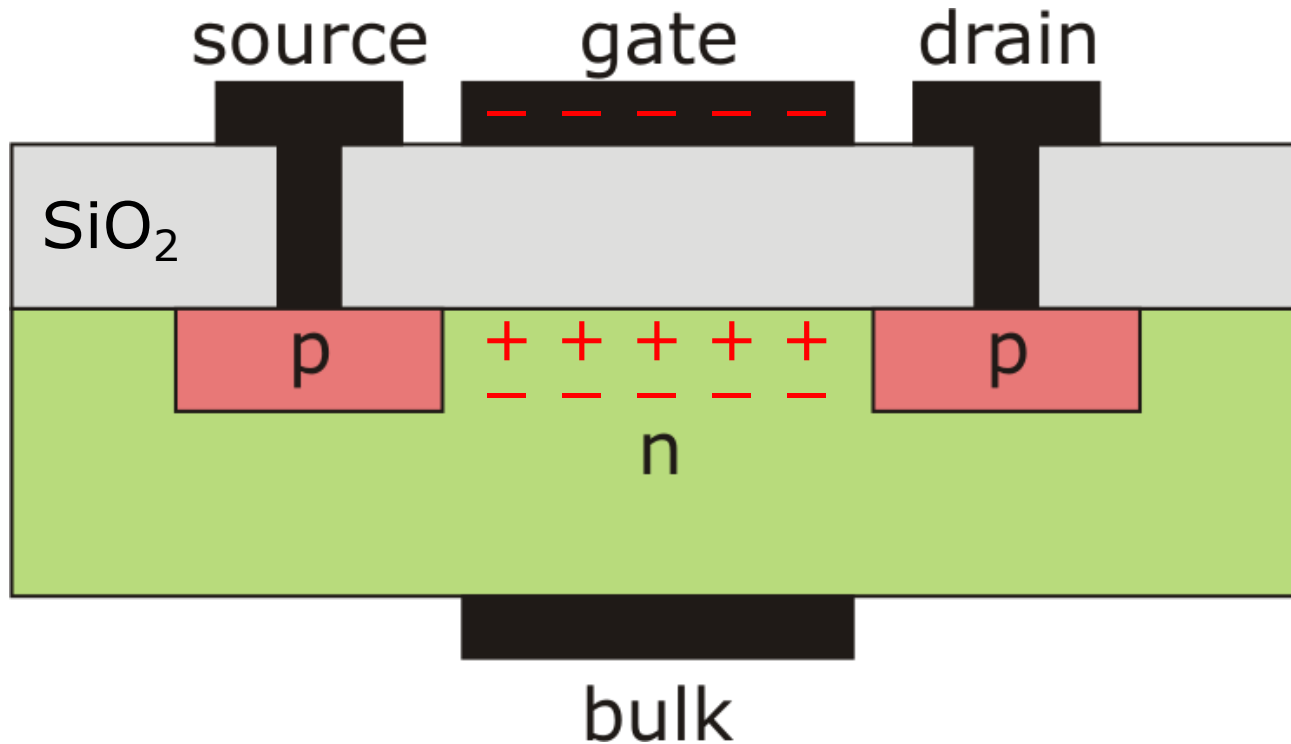
- Modular data acquisition system
- Ethernet interface
- 1 × HV up to 2000 V,  $\leq 1$  W
- 4 × Charge-integrating amplifier  
 Ranges: 0...50 pC – 0...1.8 nC  
 Integration time: 1 ms – 1 s
- 20-bit ADC
- Noise w/ Fermi chamber:  $<0.4 \mu\text{Gy/h}$



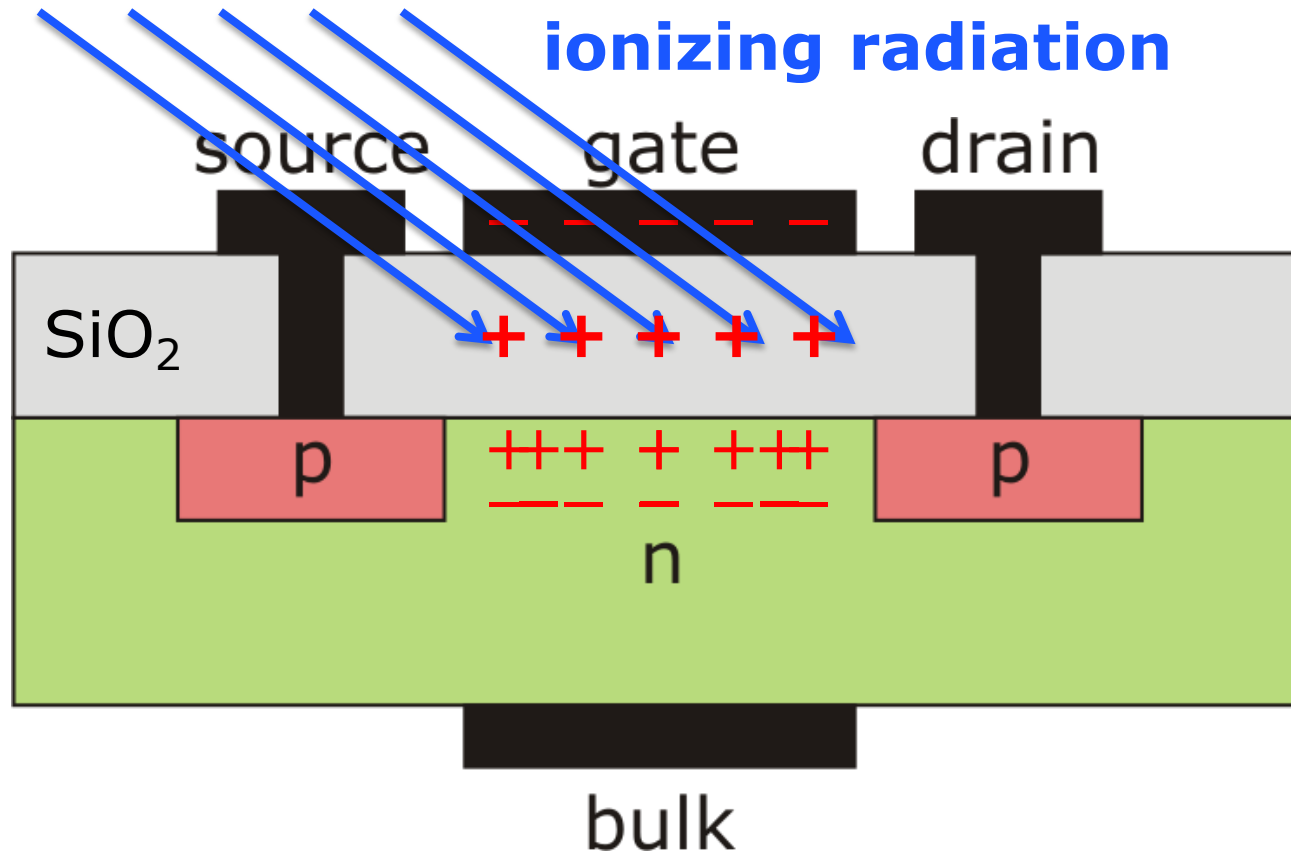
- Air filled chamber
- Charges collected:
  - Electrons
  - Oxygen ions ( $O_2^-$ )
  - Positive ions ( $N_2^+$  etc.)
- Integration time: 3 ms (2 ms sufficient to collect all charges)



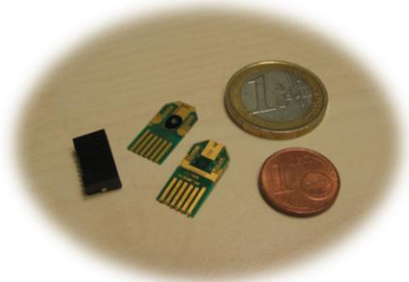
# Online Solid-State Dosimetry



negative gate potential → conductive inversion layer

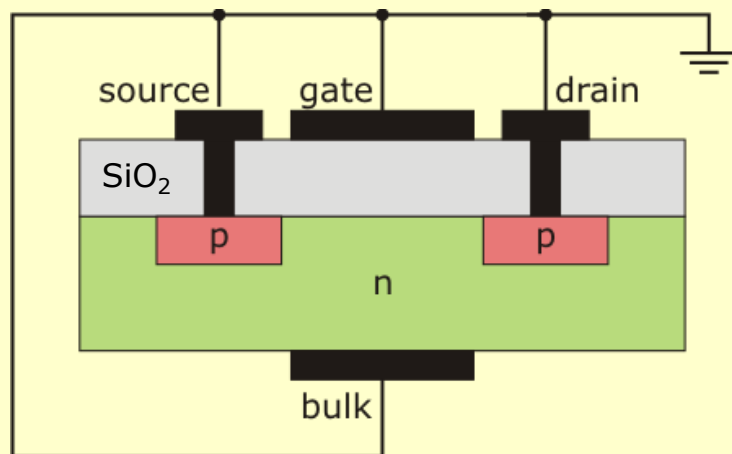


ionizing radiation → stationary charges in insulation layer

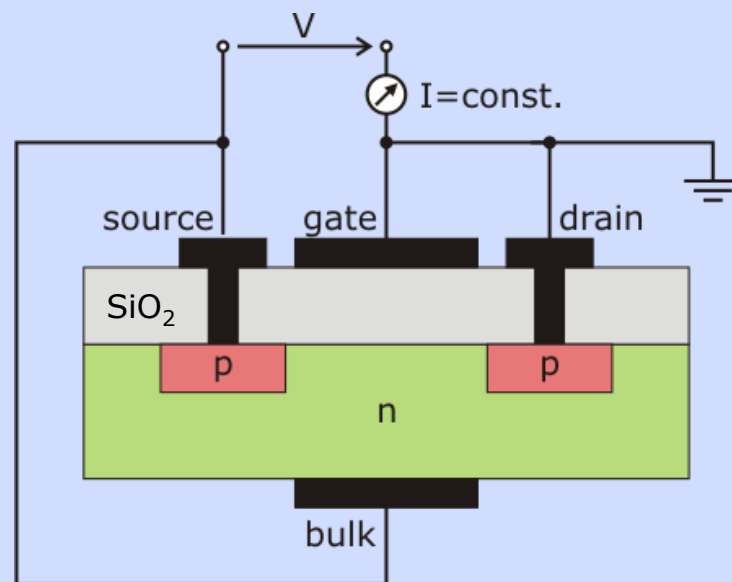


- REM Oxford Ltd. RADFET RFT-300-CC10G1
- Chip contains 2 p-channel MOSFETs with 300 nm insulator layer

exposure  
"zero bias"



read-out



Track voltage for constant current (490  $\mu\text{A}$ ) between source and drain

## L01-DOSFET

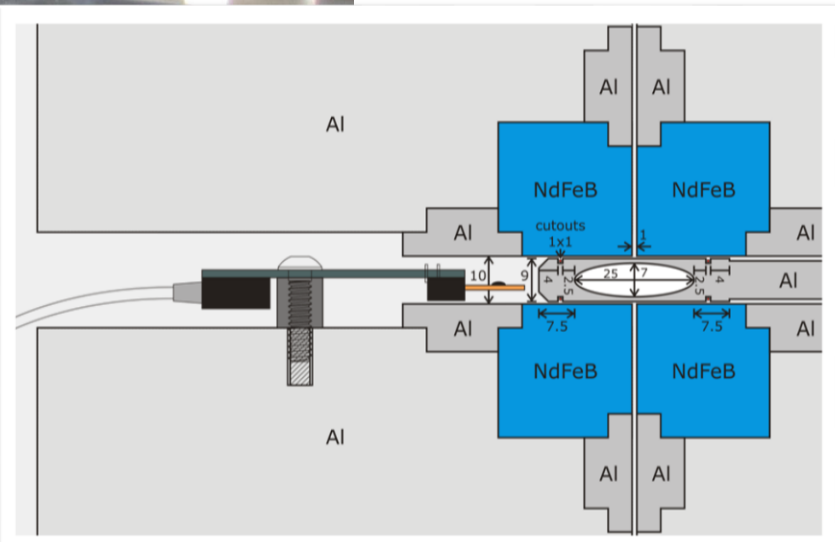
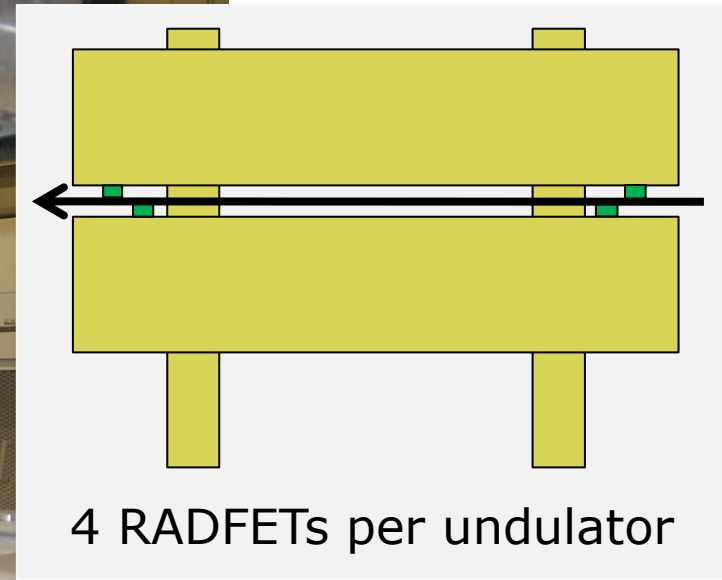
- Ethernet interface
- 4 RADFET channels
- Fixed read-out current: 490  $\mu$ A
- Voltage read-out: 24 bit ADC, up to 25 V
- Programmable interlock output
- Uses standard USB cables

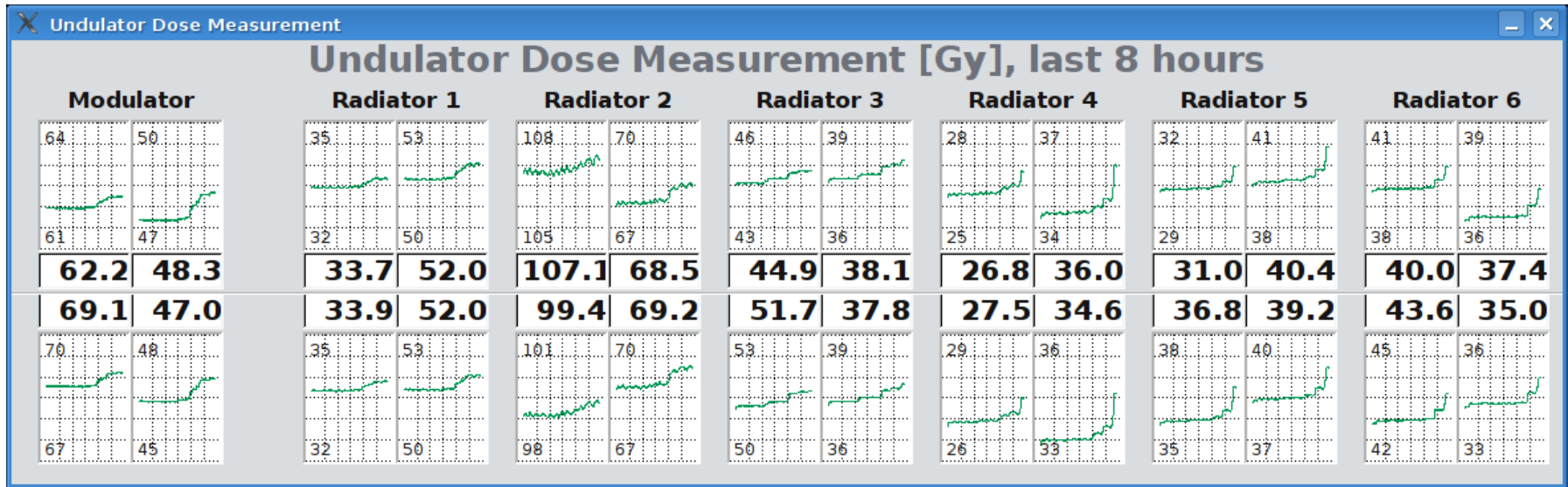


Photo: M. Peloi

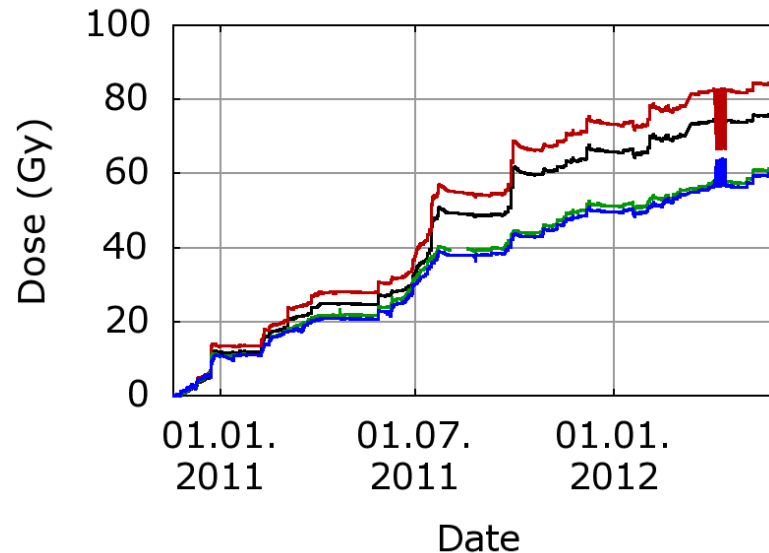








First undulator of FEL-1:



upstream bottom  
 upstream top  
 downstream top  
 downstream bottom

# Thanks for your interest.

Many thanks to:

- Mario Ferianis, Alessandro Carniel, and the instrumentation and controls groups of Sincrotrone Trieste
- Arne Miller (Risø High Dose Reference Laboratory, DK)
- Andrew Holmes-Siedle (REM Oxford Ltd., UK)